



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
ATTY. DOCKET NO. 50422-5

In re Patent Application of Steve Hill

Serial No. 10/761,338 (Unofficial)

Group Art Unit: 2874

Filed: January 22, 2004

Examiner:

For: BROADBAND OPTICAL PUMP SOURCE FOR OPTICAL AMPLIFIERS, PLANAR OPTICAL AMPLIFIERS, PLANAR OPTICAL CIRCUITS AND PLANAR OPTICAL LASERS
FABRICATED USING GROUP IV SEMICONDUCTOR NANOCRYSTALS

INFORMATION DISCLOSURE STATEMENT

This Information Disclosure Statement is being filed in the manner prescribed by 37 CFR 1.97(b) - (d) to satisfy the duty under 37 CFR 1.56 to disclose to the Office information, known to individuals associated with the filing and prosecution of the subject application, which is material to the examination of the application.

In accordance with 37 CFR 1.97(g) and (h), this statement is not to be construed as a representation that a search has been made or an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 CFR 1.56(b).

This information disclosure statement is being filed within three months of the filing date of a national application, within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or before the mailing date of a first official action on the merits and therefore applicant respectfully requests consideration under 37 CFR 1.97(b).

In compliance with 37 CFR 1.98(a)(1), a list of all patents, publications or other information submitted for consideration by the Office is hereby provided by way of the attached Form PTO 1449.

In compliance with 37 CFR 1.98(a)(2), also enclosed is a legible copy of:

- i) each United States and foreign patent;
- ii) each publication or that portion which caused it to be listed; and
- iii) all other information or that portion which caused it to be listed, excluding any copies of a United States patent application.

It is respectfully requested that the information be expressly considered by the Examiner and that the references be made of record and appear among the "References Cited" on any patent to issue therefrom.

The Patent Office is hereby authorized to charge any deficiency, or credit any overpayment in fees to Deposit Account Number 19-2550.

Respectfully submitted,

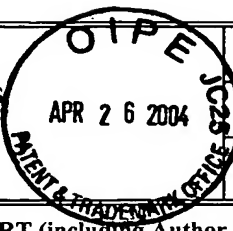
STEVE HILL

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Dated: April 21, 2004

Encls.: Form PTO-1449
All references listed on Form PTO-1449
Acknowledgement Card

Form PTO-1449 (Modified)	Atty. Docket No. 50422-5	Serial No. 10/761,338
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	Applicant Steve Hill	
	Filing Date January 22, 2004	Group 2874



OTHER ART (including Author, Title, Date, Pertinent Pages, Etc.)

AP	Georgia Franzò, et al.; Er ³⁺ IONS-Si NANOCRYSTALS INTERACTIONS AND THEIR EFFECTS ON THE LUMINESCENCE PROPERTIES; Applied Physics Letters, Vol. 76, No. 16, 17 April 2000, pp. 2167-2169.
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AR	Jung H. Shin, et al.; PHOTOLUMINESCENCE EXCITATION SPECTROSCOPY OF ERBIUM-DOPED SILICON-RICH SILICON OXIDE; Applied Physics Letters, Vol. 76, No. 15, 10 April 2000, pp. 1999-2001.
AS	F. Iacona, et al.; ELECTROLUMINESCENCE AT 1.54 µm IN Er-DOPED Si NANOCUSTER-BASED DEVICES; Applied Physics Letters, Vol. 81, No. 17, 21 October 2002, pp. 3242-3244.
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AU	A.J. Kenyon, et al.; LUMINESCENCE FROM ERBIUM-DOPED SILICON NANOCRYSTALS IN SILICA: EXCITATION MECHANISMS; Journal of Applied Physics, Vol. 91, No. 1, 1 January 2002, pp. 367-374.
AV	J. De la Torre, et al.; OPTICAL AND ELECTRICAL TRANSPORT MECHANISMS IN Si-NANOCRYSTAL-BASED LEDs; Elsevier Science B.V., Physica E, 2002, pp. 1-3.
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AX	P.G. Kik, et al.; STRONG EXCITON-ERBIUM COUPLING IN Si NANOCRYSTAL-DOPED SiO ₂ ; Applied Physics Letters, Vol. 76, No. 17, 24 April 2000, pp. 2325-2327.
AY	G. Franzò, et al.; ELECTROLUMINESCENCE OF SILICON NANOCRYSTALS IN MOS STRUCTURES; Appl. Phys. A, Materials Science & Processing, 74, (2002), pp. 1-5.
AZ	A. Irrera, et al.; EXCITATION AND DE-EXCITATION PROPERTIES OF SILICON QUANTRUM DOTS UNDER ELECTRICAL PUMPING; Applied Physics Letters, Vol. 81, No. 10, 2 September 2002, pp. 1866-1868.
aa	P.S. Andry, et al.; GROWTH OF Er-DOPED SILICON USING METALORGANICS BY PLASMA-ENHANCED CHEMICAL VAPOR DEPOSITION; J. Appl. Phys. 80 (1), 1 July 1996, pp. 551-558.
ab	Kei Watanabe, et al.; RESONANT EXCITATION OF Er ³⁺ BY THE ENERGY TRANSFER FROM Si NANOCRYSTALS; Journal of Applied Physics, Vol. 90, No. 9, 1 November 2001, pp. 4761-4767.
ac	J. De la Torre, et al.; OPTICAL PROPERTIES OF SILICON NANOCRYSTAL LEDs; Elsevier Science B.V., Physica E, 2002, pp. 326-330.

EXAMINER	DATE CONSIDERED
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EXAMINER:

Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

